N-Channel 30-V (D-S) MOSFET

Key Features:

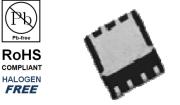
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- Fast switching speed

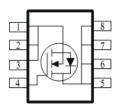
Typical Applications:

- Synchronous Buck DC/DC Conversion
- Synchronous Rectification
- Power Routing and ORing

| PRODUCT SUMMARY | | | |
|-----------------|-----------------------------|-------|--|
| Vds (V) | $r_{DS(on)}(m\Omega)$ | I⊳(A) | |
| 30 | 2.8 @ V _{GS} = 10V | 35 | |
| 30 | 4 @ V _{GS} = 4.5V | 29 | |

DFN5X6-8L





| ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED) | | | | | | | |
|------------------------------------------------------------------------|----------------------|-----------------------------------|------------|-------|--|--|--|
| Parameter | | Symbol | Limit | Units | | | |
| Drain-Source Voltage | V _{DS} | 30 | V | | | | |
| Gate-Source Voltage | | V _{GS} | ±20 | V | | | |
| Continuous Drain Current ^a | T _A =25°C | I _D | 35 | | | | |
| | T _A =70°C | | 28 | А | | | |
| Pulsed Drain Current ^b | | I _{DM} 100 | | | | | |
| Continuous Source Current (Diode Conduction) ^a | | ۱ _s | 7.3 | А | | | |
| Dower Dissinction ^a | T _A =25°C | P _D | 5 | W | | | |
| Power Dissipation ^a | T _A =70°C | U 'D | 3.2 | vv | | | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | -55 to 150 | °C | | | |

| THERMAL RESISTANCE RATINGS | | | | | | |
|------------------------------------------|--------------|--------------------|-------|------|--|--|
| Parameter | Symbol | Maximum | Units | | | |
| Maximum Junction-to-Ambient ^a | t <= 10 sec | R _{eja} | 25 | °C/W | | |
| | Steady State | ιν _θ ja | 65 | C/VV | | |

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

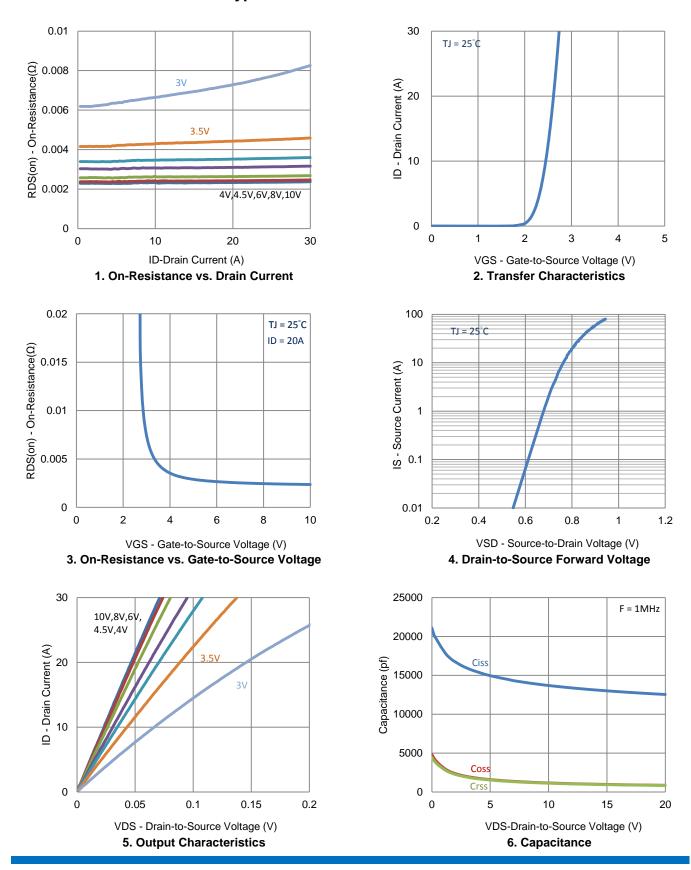
Electrical Characteristics

| Parameter | Symbol | Test Conditions | Min | Тур | Max | Unit | |
|-----------------------------------------|------------------------|----------------------------------------------------------------------------------|-----|-------|------|------|--|
| Static | | | | | | | |
| Gate-Source Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_D = 250 \text{ uA}$ | 1 | | | V | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | | ±100 | nA | |
| Zero Gate Voltage Drain Current | | $V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$ | | | 1 | uA | |
| Zero Gale Voltage Dialit Current | DSS | $V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$ | | | 25 | | |
| On-State Drain Current ^a | I _{D(on)} | $V_{DS} = 5 V, V_{GS} = 10 V$ | 50 | | | А | |
| Ducia Course On Desistance a | r | $V_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$ | | | 2.8 | | |
| Drain-Source On-Resistance ^a | r _{DS(on)} | $V_{GS} = 4.5 \text{ V}, I_{D} = 16 \text{ A}$ | | | 4 | mΩ | |
| Forward Transconductance ^a | g _{fs} | $V_{DS} = 15 \text{ V}, \text{ I}_{D} = 20 \text{ A}$ | | 26 | | S | |
| Diode Forward Voltage ^a | V_{SD} | $I_{S} = 3.7 \text{ A}, V_{GS} = 0 \text{ V}$ | | 0.73 | | V | |
| | | Dynamic ^b | | | | | |
| Total Gate Charge | Qg | V _{DS} = 15 V, V _{GS} = 4.5 V, | | 64 | | nC | |
| Gate-Source Charge | Q _{gs} | $V_{DS} = 13 V, V_{GS} = 4.3 V,$ $I_{D} = 20 A$ | | 17 | | | |
| Gate-Drain Charge | Q _{gd} | 1 _D = 20 A | | 32 | | | |
| Turn-On Delay Time | t _{d(on)} | $V_{DS} = 15 \text{ V}, \text{ R}_{L} = 0.8 \Omega,$ | | 17 | | | |
| Rise Time | t _r | $V_{\rm DS} = 15$ V, $N_{\rm L} = 0.8$ $\Omega_{\rm c}$, $I_{\rm D} = 20$ A, | | 28 | | ns | |
| Turn-Off Delay Time | t _{d(off)} | $V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{GEN}} = 6 \Omega$ | | 168 | | | |
| Fall Time | t _f | $V_{\text{GEN}} = 10$ V, $V_{\text{GEN}} = 0.22$ | | 65 | | | |
| Input Capacitance | C _{iss} | | | 13001 | | | |
| Output Capacitance | C _{oss} | $V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$ | | 966 | | pF | |
| Reverse Transfer Capacitance | C _{rss} | | | 939 | | | |

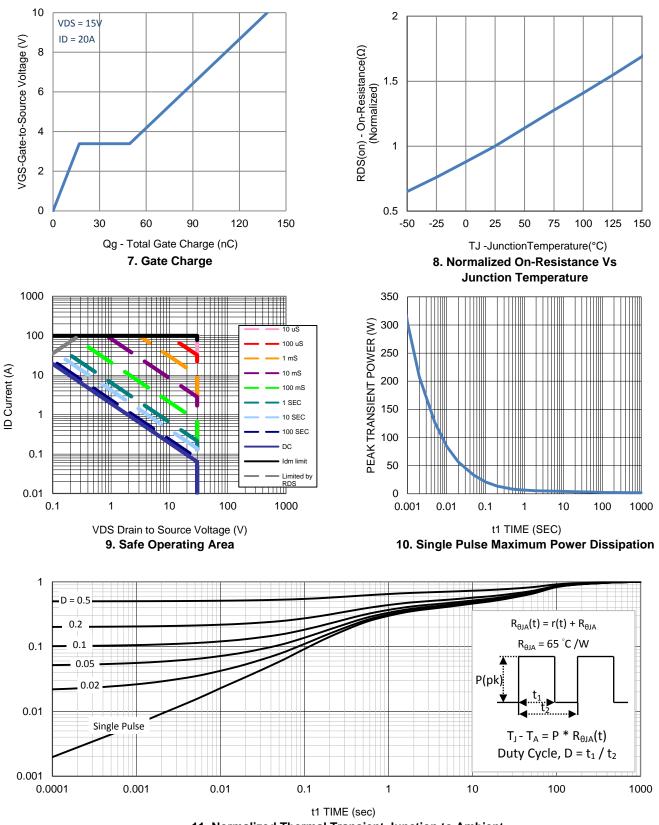
Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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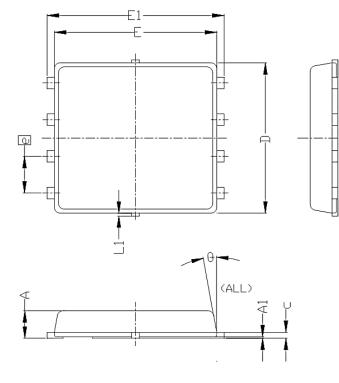
Typical Electrical Characteristics

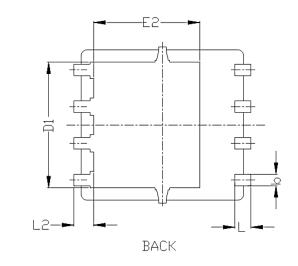


Typical Electrical Characteristics

11. Normalized Thermal Transient Junction to Ambient

Package Information





| SYMBOLS | DIMENSIONS IN MILLIMETERS | | | DIMENSIONS IN INCHES | | | |
|---------|---------------------------|----------------------|------|----------------------|-------|-------|--|
| STMBULS | MIN | NOM | MAX | MIN | NOM | MAX | |
| Α | 0.85 | 0.95 | 1.00 | 0.033 | 0.037 | 0.039 | |
| Al | 0.00 | | 0.05 | 0.000 | | 0.002 | |
| b | 0.30 | 0.40 | 0.50 | 0.012 | 0.016 | 0.020 | |
| с | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 | |
| D | | 5.20 BSC | | 0.205 BSC | | | |
| D1 | | 4. 35 BSC 0. 171 BSC | | | | | |
| | | | | | | | |
| E | 5.55 BSC | | | 0.219 BSC | | | |
| E1 | 6.05 BSC | | | 0.238 BSC | | | |
| E2 | 3.62 BSC | | | 0. 143 BSC | | | |
| e | 1.27 BSC | | | 0.050 BSC | | | |
| L | 0.45 | 0.55 | 0.65 | 0.018 | 0.022 | 0.026 | |
| L1 | 0 | | 0.15 | 0 | | 0.006 | |
| L2 | 0.68 REF | | | 0.027 REF | | | |
| θ | 0° | | 10° | 0° | | 10° | |